

Large area etching for porous semiconductors

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Abstract

While electrochemical etching of small samples in the 1 cm region is relatively easy, this is not true for large areas, i.e. standard wafer sizes up to 300 mm. The paper outlines the specific demands and difficulties in some detail, discusses large area etching strategies and systems, in particular for very deep macropores, and presents and discusses various results from the large area etching system of the authors.